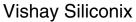
SiA923EDJ





Dual P-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A)	Q _g (Typ.)	
- 20	0.054 at V _{GS} = - 4.5 V	- 4.5 ^a		
	0.070 at V _{GS} = - 2.5 V	- 4.5 ^a	9.5 nC	
	0.104 at V _{GS} = - 1.8 V	- 4.5 ^a	9.5110	
	0.165 at V _{GS} = - 1.5 V	- 1.5		

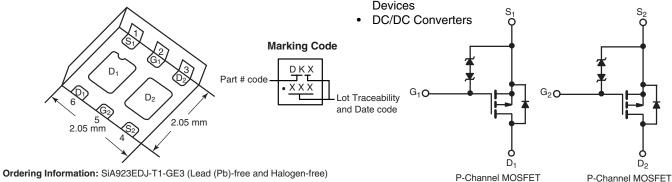
PowerPAK SC-70-6 Dual

FEATURES

- Halogen-free According to IEC 61249-2-21
 Definition
- TrenchFET[®] Power MOSFET
- New Thermally Enhanced PowerPAK[®] SC-70
 Package
 - Small Footprint Area
 - Low On-Resistance
- Typical ESD Protection: 2500 V
- 100 % R_q Tested
- Compliant to RoHS Directive 2002/95/EC

APPLICATIONS

Charger Switches and Load Switches for Portable
 Devices



ABSOLUTE MAXIMUM RATINGS	T _A = 25 °C, unles	ss otherwise no	ted		
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	- 20	v	
Gate-Source Voltage		V _{GS}	± 8	- v	
	T _C = 25 °C		- 4.5 ^a		
Continuous Drain Current ($T_1 = 150 \ ^{\circ}C$)	T _C = 70 °C	I _D	- 4.5 ^a		
	T _A = 25 °C	טי	- 4.5 ^{a, b, c}		
	T _A = 70 °C	Γ	- 4.5 ^{a, b, c}	A	
Pulsed Drain Current		I _{DM}	- 15		
Continuous Source-Drain Diode Current	T _C = 25 °C	I _S	- 4.5 ^a		
	T _A = 25 °C	'5	- 1.6 ^{b, c}		
	T _C = 25 °C		7.8		
Maximum Power Dissipation	T _C = 70 °C	PD	5	w	
	T _A = 25 °C		1.9 ^{b, c}	~~~~	
	T _A = 70 °C		1.2 ^{b, c}	<u> </u>	
Operating Junction and Storage Temperature Ra	T _J , T _{stg}	- 55 to 150	°C		
Soldering Recommendations (Peak Temperature) ^{d, e}			260	- v	

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{b, f}	t ≤ 5 s	R _{thJA}	52	65	°C/W	
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	12.5	16		

Notes:

a. Package limited.

b. Surface mounted on 1" x 1" FR4 board.

c. t = 5 s.

d. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

f. Maximum under steady state conditions is 110 °C/W.



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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static						•	
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, \text{ I}_{D} = -250 \mu\text{A}$	- 20			V	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I _D = - 250 μA		- 15		mV/°C	
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	i _D = - 230 μA		2.5			
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \ \mu A$	- 0.5		- 1.4	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$		± 0.3	± 3	μΑ	
		$V_{DS} = 0 V, V_{GS} = \pm 8 V$		± 3	± 30		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}$			- 1		
		V_{DS} = - 20 V, V_{GS} = 0 V, T_{J} = 55 °C			- 10		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le$ - 5 V, V_{GS} = - 4.5 V	- 15			А	
Drain-Source On-State Resistance ^a	(-)	V _{GS} = - 4.5 V, I _D = - 3.8 A		0.044	0.054	1	
		V _{GS} = - 2.5 V, I _D = - 3.3 A		0.057	0.070	- Ω	
	R _{DS(on)}	V _{GS} = - 1.8 V, I _D = - 1 A		0.075	0.104		
		V _{GS} = - 1.5 V, I _D = - 0.5 A		0.097	0.165		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 10 V, I _D = - 3.8 A		11		S	
Dynamic ^b					1	<u> </u>	
Total Gate Charge	Qg	V_{DS} = - 10 V, V_{GS} = - 8 V, I_{D} = - 4.9 A		16.3	25	nC	
				9.5	14.5		
Gate-Source Charge	Q _{gs}	V_{DS} = - 10 V, V_{GS} = - 4.5 V, I_{D} = - 4.9 A		1.4			
Gate-Drain Charge	Q _{gd}			2.3			
Gate Resistance	Rg	f = 1 MHz	1	5.1	10	Ω	
Turn-On Delay Time	t _{d(on)}			15	25		
Rise Time	t _r	V_{DD} = - 10 V, R _L = 2.6 Ω		16	25		
Turn-Off Delay Time	t _{d(off)}	${\rm I_D}\cong$ - 3.9 A, ${\rm V_{GEN}}$ = - 4.5 V, ${\rm R_g}$ = 1 Ω		30	45	1	
Fall Time	t _f	-		10	15		
Turn-On Delay Time	t _{d(on)}			7	15	- ns - -	
Rise Time	t _r	V_{DD} = - 10 V, R _L = 2.6 Ω		12	20		
Turn-Off Delay Time	t _{d(off)}	$\rm I_D \cong$ - 3.9 A, $\rm V_{GEN}$ = - 8 V, $\rm R_g$ = 1 Ω		26	40		
Fall Time	t _f			10	15		
Drain-Source Body Diode Characterist	ics			1			
Continuous Source-Drain Diode Current	ا _S	T _C = 25 °C			- 4.5	A	
Pulse Diode Forward Current	I _{SM}				- 15		
Body Diode Voltage	V _{SD}	$I_{\rm S}$ = - 3.9 A, $V_{\rm GS}$ = 0 V		- 0.9	- 1.2	V	
Body Diode Reverse Recovery Time	t _{rr}			13	25	ns	
Body Diode Reverse Recovery Charge	Diode Beverse Becovery Charge			5.5	12	nC	
Reverse Recovery Fall Time	t _a	$I_F = -3.9 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, \text{ T}_J = 25 ^\circ\text{C}$		7.5			
Reverse Recovery Rise Time	t _b			5.5	1	ns	

Notes:

a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

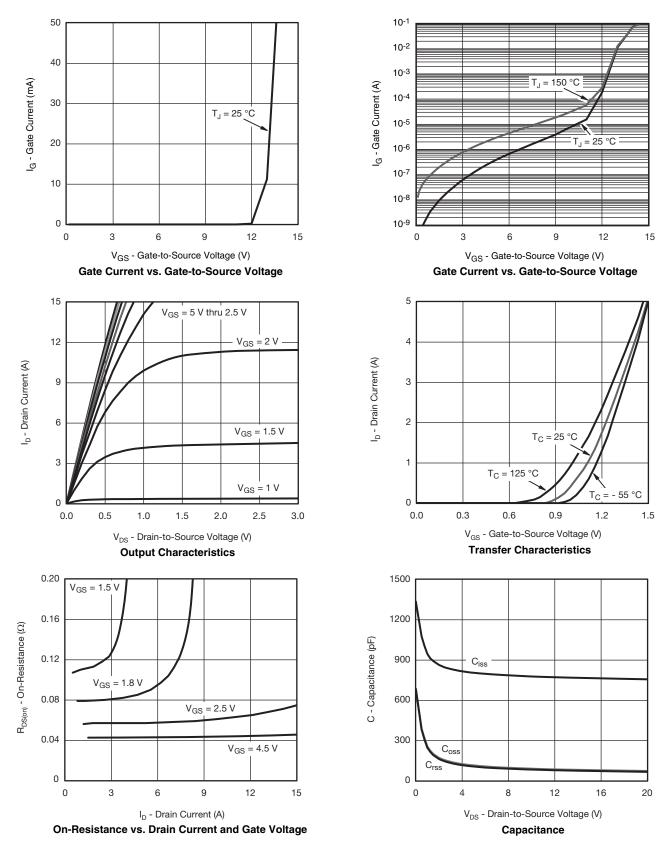
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



SiA923EDJ Vishay Siliconix

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



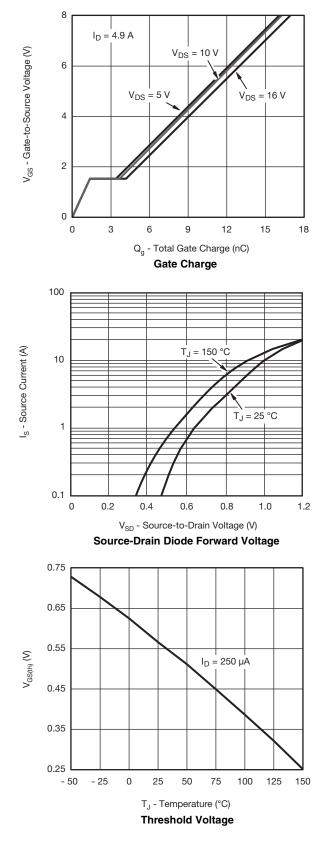
Document Number: 66803 S10-1535-Rev. A, 19-Jul-10

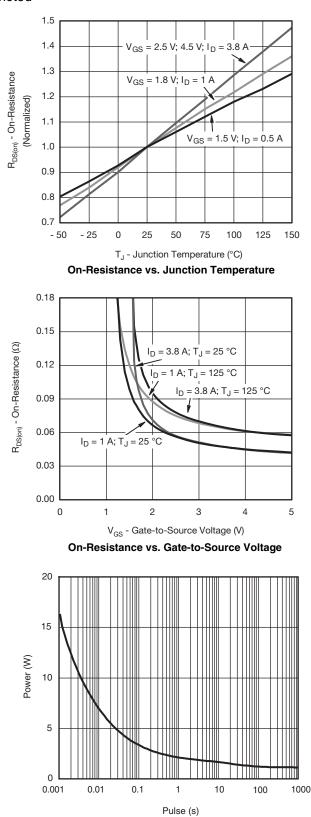
SiA923EDJ

Vishay Siliconix



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



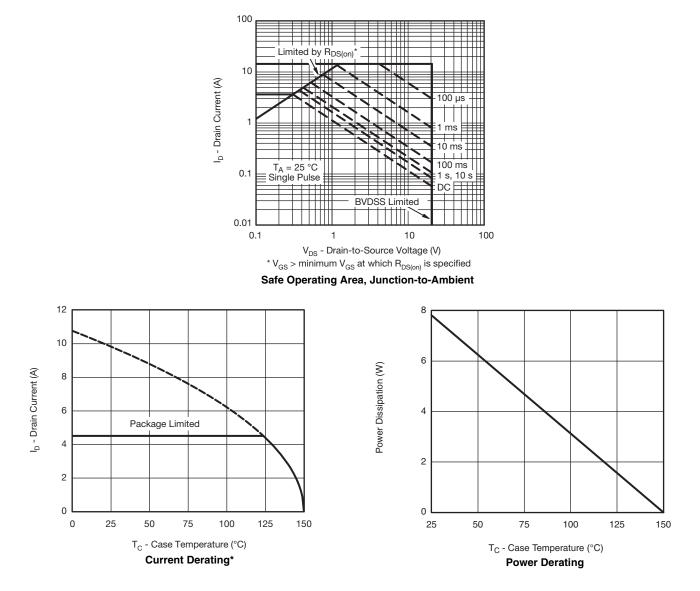


Single Pulse Power, Junction-to-Ambient



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

VISHAY



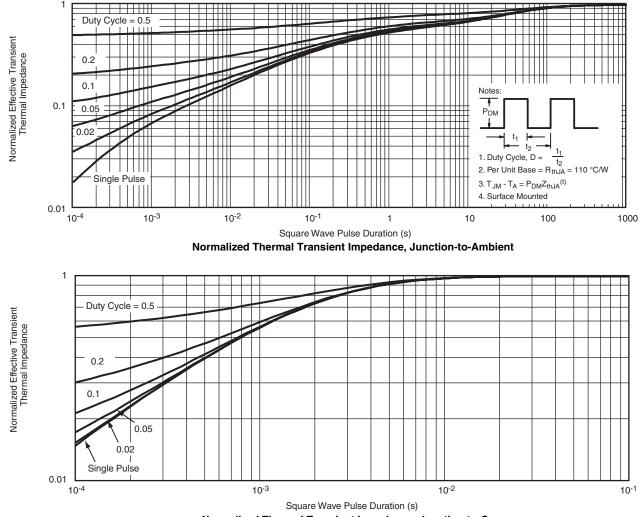
* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

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Vishay Siliconix

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?66803.



PowerPAK[®] SC70-6L

VISHA

b PIN2 PIN1 PIN3 _ ₹



b

PIN3

__ ₿

PIN2

PIN1

¥

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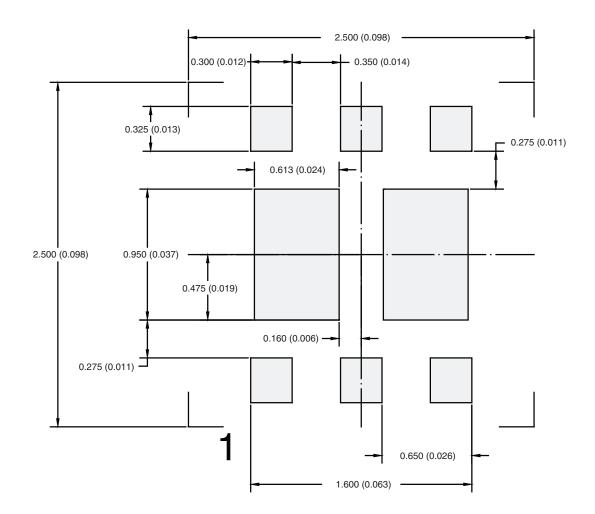
¹

Application Note 826

Vishay Siliconix



RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Dual



Dimensions in mm (inches)

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Vishay

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